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IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-8 (cancelled)

9.   (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in~~comprising the steps of ~~that~~ maintaining_a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is at~~ less than 500°C ~~or less~~, and maintaining_a temperature ramping rate in a temperature range from the heat treatment temperature at initial entry to ~~an~~ ~~ultimate~~a maximum temperature ~~set~~in a range of 700°C - 900°C, ~~is set to~~said ramping rate being 1°C/min or less.

10.   (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in~~comprising the steps of ~~that~~ maintaining_a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is at~~ less than 500°C ~~or less~~, and maintaining_a temperature ramping rate in a temperature range from the heat treatment temperature at initial entry to ~~an~~ ~~ultimate~~a maximum temperature ~~set~~in a range of 700°C - 900°C, said ramping rate being ~~is set~~ to 1°C/min or less, so as to make uniform the distribution of an oxide precipitate density of the silicon single crystal wafer after heat treatment.

11.   (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, comprising the steps of ~~characterized in~~ that ~~a~~controlling heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment and controlling_a temperature ramping rate from the heat treatment